

AMENDMENTS TO THE SPECIFICATION:

Please delete the 4-line long paragraph beginning at page 1, line 6.

Please amend the paragraph beginning at page 11, line 13, as follows:

A second semiconductor device production method according to an example of the present invention comprises the steps of: (e) forming an insulative film on an underlying substrate and patterning ~~patter~~ing the insulative film to form a recess in the insulative film; (f) forming a semiconductor layer on the insulative film, the semiconductor layer having a thick film portion located on a portion of the insulative film formed with the recess and a thin film portion located on a portion of the insulative film adjacent to the recess; (g) separating the semiconductor layer on the flexible substrate from the insulative film on the underlying substrate; and (h) bonding a flexible substrate onto a surface of the separated semiconductor layer which has been opposed to the underlying substrate.